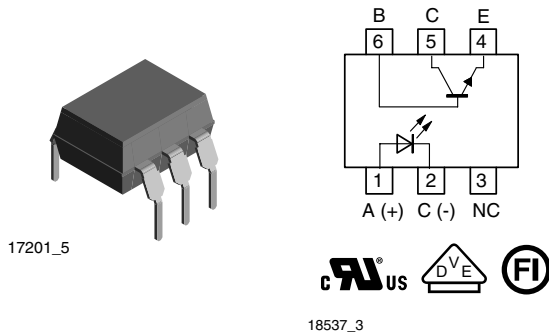


# Optocoupler, Phototransistor Output, with Base Connection



## DESCRIPTION

The CNY17G consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6 pin plastic dual in line package.

## AGENCY APPROVALS

- UL1577, file no. E52744, double protection
- BSI: BS EN 60065, BS EN 60950-1
- DIN EN 60747-5-5 (VDE 0884)
- FIMKO (SETI): EN 60950, certificate no. FI25155

## FEATURES

- Isolation materials according to UL94V-O
- Pollution degree 2 (DIN/VDE 0110 part 1 resp. IEC 60664)
- Climatic classification 55/110/21 (IEC 60068 part 1)
- Special construction: therefore, extra low coupling capacity of typical 0.3 pF, high common mode rejection
- Low temperature coefficient of CTR
- Rated impulse voltage (transient overvoltage)  $V_{IOTM} = 6$  kV peak
- Isolation test voltage (partial discharge test voltage)  $V_{pd} = 1.6$  kV
- Rated isolation voltage  $V_{IORM} = 850$  V<sub>RMS</sub>
- Thickness through insulation = 0.4 mm
- Creepage current resistance according to VDE 0303/IEC 60112 comparative tracking index: CTI = 275
- CTR offered in 4 groups
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



**RoHS**  
COMPLIANT

## APPLICATIONS

- Switch-mode power supplies
- Line receiver
- Computer peripheral interface
- Microprocessor system interface
- Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):
  - for appl. class I - IV at mains voltage  $\leq 300$  V
  - for appl. class I - III at mains voltage  $\leq 600$  V according to DIN EN 60747-5-5 (VDE 0884)

## ORDER INFORMATION

PART	REMARKS
CNY17G-1	CTR 40 % to 80 %, DIP-6
CNY17G-2	CTR 63 % to 125 %, DIP-6
CNY17G-3	CTR 100 % to 200 %, DIP-6
CNY17G-4	CTR 160 % to 320 %, DIP-6

### Note

G = leadform 10.16 mm; G is not marked on the body.

Vishay Semiconductors Optocoupler, Phototransistor Output,  
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ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>INPUT</b>				
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	60	mA
Forward surge current	$t_p \leq 10 \mu s$	$I_{FSM}$	3	A
Power dissipation		$P_{diss}$	100	mW
Junction temperature		$T_j$	125	°C
<b>OUTPUT</b>				
Collector emitter voltage		$V_{CEO}$	32	V
Emitter collector voltage		$V_{ECO}$	7	V
Collector current		$I_C$	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10 ms$	$I_{CM}$	100	mA
Power dissipation		$P_{diss}$	150	mW
Junction temperature		$T_j$	125	°C
<b>COUPLER</b>				
Isolation test voltage (RMS)		$V_{ISO}$	5000	$V_{RMS}$
Total power dissipation		$P_{tot}$	250	mW
Ambient temperature range		$T_{amb}$	- 55 to + 110	°C
Storage temperature range		$T_{stg}$	- 55 to + 125	°C
Soldering temperature <sup>(2)</sup>	2 mm from case, $t \leq 10 s$	$T_{sld}$	260	°C

**Notes**

- (1)  $T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified.  
Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.
- (2) Refer to wave profile for soldering conditions for through hole devices.

ELECTRICAL CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>INPUT</b>						
Forward voltage	$I_F = 50 \text{ mA}$	$V_F$		1.25	1.6	V
Junction capacitance	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$	$C_j$		50		pF
Reverse current	$V_R = 5 \text{ V}$	$I_R$			10	$\mu\text{A}$
<b>OUTPUT</b>						
Collector emitter voltage	$I_C = 1 \text{ mA}$	$V_{CEO}$	32			V
Emitter collector voltage	$I_E = 100 \mu\text{A}$	$V_{ECO}$	7			V
Collector emitter cut-off current	$V_{CE} = 10 \text{ V}, I_F = 0$	$I_{CEO}$		10	100	nA
<b>COUPLER</b>						
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	$V_{CEsat}$			0.3	V
Cut-off frequency	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 100 \Omega$	$f_c$		110		kHz
Coupling capacitance	$f = 1 \text{ MHz}$	$C_k$		0.3		pF

**Note**

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified.  
Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
$I_C/I_F$	$V_{CE} = 5\text{ V}, I_F = 10\text{ mA}$	CNY17G-1	CTR	40		80	%
		CNY17G-2	CTR	63		125	%
		CNY17G-3	CTR	100		200	%
		CNY17G-4	CTR	160		320	%
	$V_{CE} = 5\text{ V}, I_F = 1\text{ mA}$	CNY17G-1	CTR	13			%
		CNY17G-2	CTR	22			%
		CNY17G-3	CTR	34			%
		CNY17G-2	CTR	56		200	%

MAXIMUM SAFETY RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>INPUT</b>						
Forward current		$I_F$			130	mA
<b>OUTPUT</b>						
Power dissipation		$P_{diss}$			265	mW
<b>COUPLER</b>						
Rated impulse voltage		$V_{IOTM}$			6	kV
Safety temperature		$T_{si}$			150	°C

**Note**

According to DIN EN 60747-5-5 (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
AC isolation test voltage (RMS)	$f = 50\text{ Hz}, t = 1\text{ s}$	$V_{ISO}$	3750			$V_{RMS}$
Tracking resistance (comparative tracking index)		CTI		275		
Partial discharge test voltage - routine test	$100\%, t_{test} = 1\text{ s}$	$V_{pd}$	1.6			kV
Partial discharge test voltage - lot test (sample test)	$t_{Tr} = 60\text{ s}, t_{test} = 10\text{ s}$ , (see figure 2)	$V_{IOTM}$	6			kV
		$V_{pd}$	1.3			kV
Insulation resistance	$V_{IO} = 500\text{ V}$	$R_{IO}$	$10^{12}$			$\Omega$
	$V_{IO} = 500\text{ V}, T_{amb} = 100\text{ °C}$	$R_{IO}$	$10^{11}$			$\Omega$
	$V_{IO} = 500\text{ V}, T_{amb} = 150\text{ °C}$ (construction test only)	$R_{IO}$	$10^9$			$\Omega$

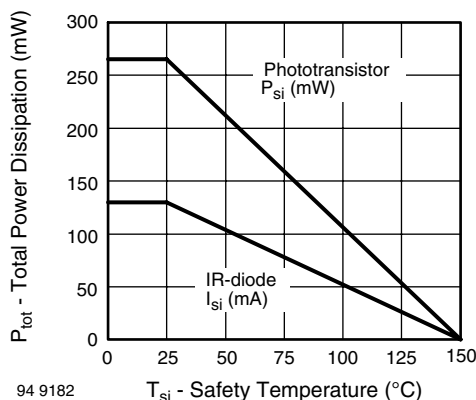
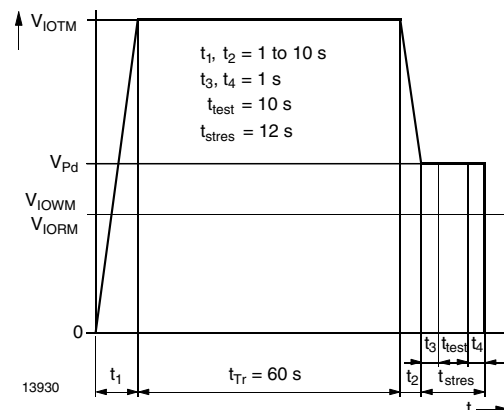


Fig. 1 - Derating Diagram


 Fig. 2 - Test Pulse Diagram for Sample Test According to  
DIN EN 60747-5-5/DIN EN 60747-; IEC 60747

SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Delay time	$V_S = 5\text{ V}$ , $I_C = 5\text{ mA}$ , $R_L = 100\ \Omega$ , (see figure 3)	$t_d$		4		$\mu\text{s}$
Rise time	$V_S = 5\text{ V}$ , $I_C = 5\text{ mA}$ , $R_L = 100\ \Omega$ , (see figure 3)	$t_r$		7		$\mu\text{s}$
Fall time	$V_S = 5\text{ V}$ , $I_C = 5\text{ mA}$ , $R_L = 100\ \Omega$ , (see figure 3)	$t_f$		6.7		$\mu\text{s}$
Storage time	$V_S = 5\text{ V}$ , $I_C = 5\text{ mA}$ , $R_L = 100\ \Omega$ , (see figure 3)	$t_s$		0.3		$\mu\text{s}$
Turn-on time	$V_S = 5\text{ V}$ , $I_C = 5\text{ mA}$ , $R_L = 100\ \Omega$ , (see figure 3)	$t_{on}$		11		$\mu\text{s}$
Turn-off time	$V_S = 5\text{ V}$ , $I_C = 5\text{ mA}$ , $R_L = 100\ \Omega$ , (see figure 3)	$t_{off}$		7		$\mu\text{s}$
Turn-on time	$V_S = 5\text{ V}$ , $I_F = 10\text{ mA}$ , $R_L = 1\text{ k}\Omega$ , (see figure 4)	$t_{on}$		25		$\mu\text{s}$
Turn-off time	$V_S = 5\text{ V}$ , $I_F = 10\text{ mA}$ , $R_L = 1\text{ k}\Omega$ , (see figure 4)	$t_{off}$		42.5		$\mu\text{s}$

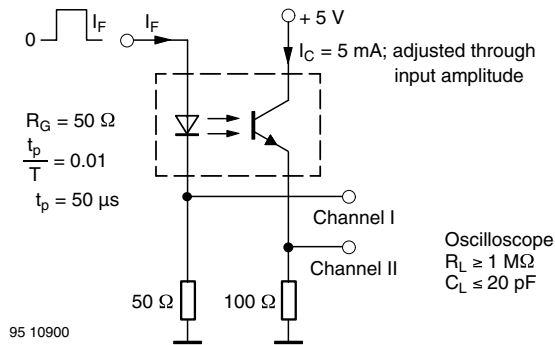


Fig. 3 - Test Circuit, Non-Saturated Operation

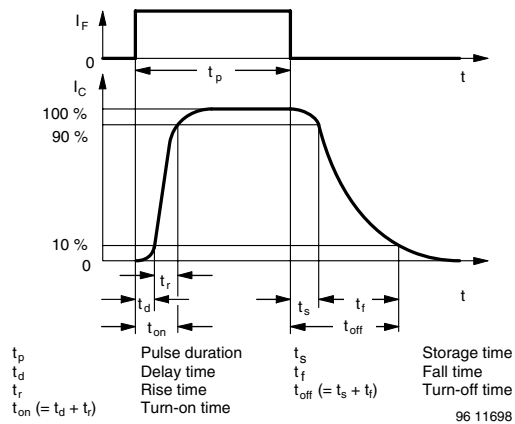


Fig. 5 - Switching Times

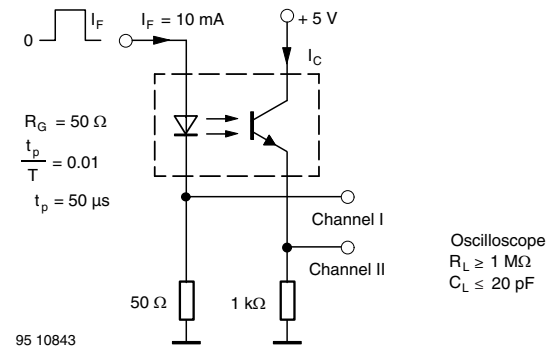


Fig. 4 - Test Circuit, Saturated Operation

**TYPICAL CHARACTERISTICS**

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

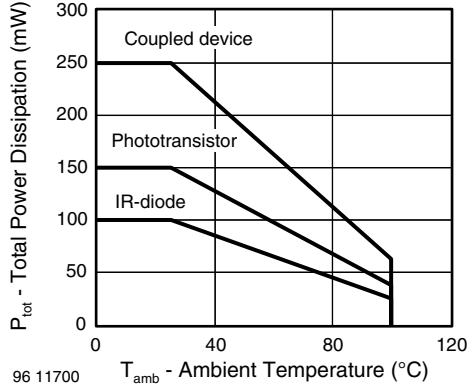


Fig. 6 - Total Power Dissipation vs. Ambient Temperature

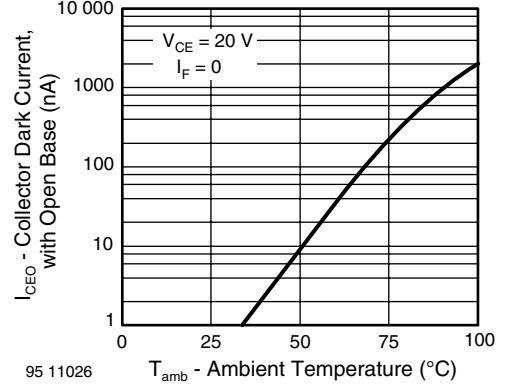


Fig. 9 - Collector Dark Current vs. Ambient Temperature

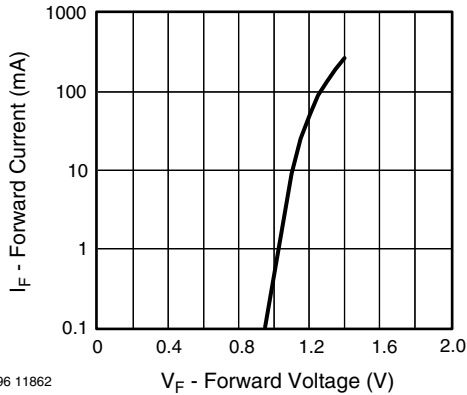


Fig. 7 - Forward Current vs. Forward Voltage

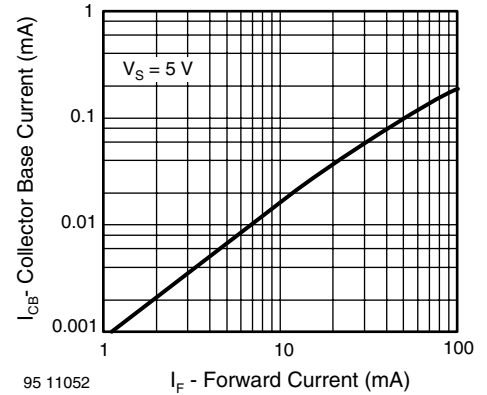


Fig. 10 - Collector Base Current vs. Forward Current

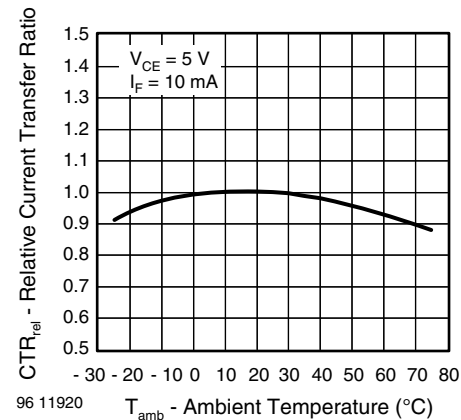


Fig. 8 - Relative Current Transfer Ratio vs. Ambient Temperature

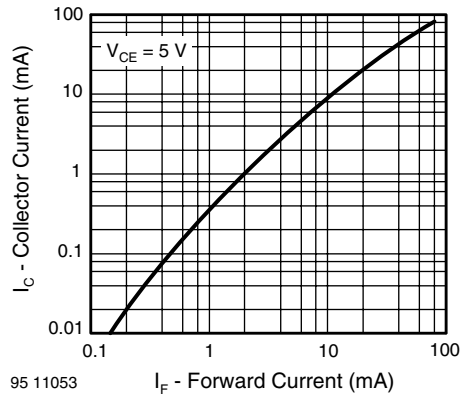


Fig. 11 - Collector Current vs. Forward Current

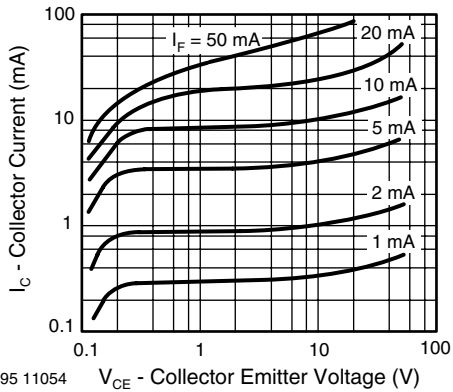


Fig. 12 - Collector Current vs. Collector Emitter Voltage

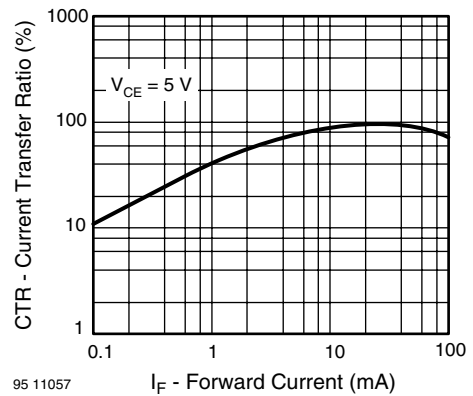


Fig. 15 - Current Transfer Ratio vs. Forward Current

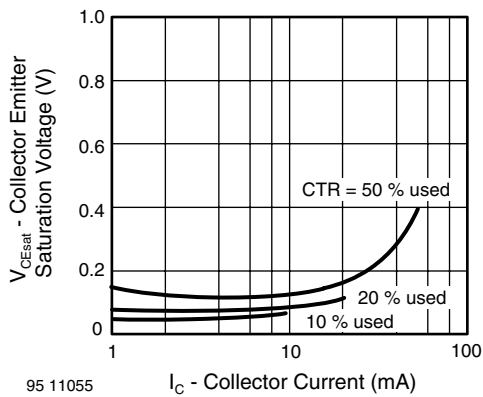


Fig. 13 - Collector Emitter Saturation Voltage vs. Collector Current

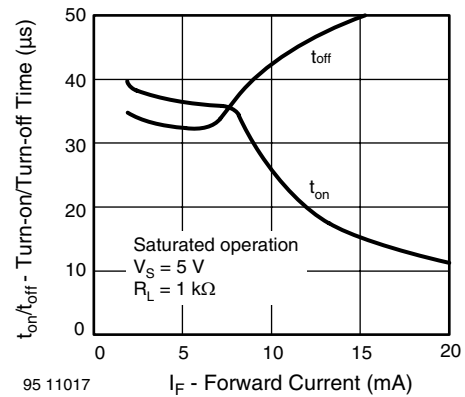


Fig. 16 - Turn-on/off Time vs. Forward Current

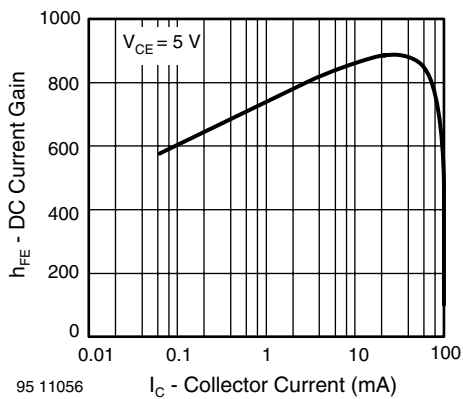


Fig. 14 - DC Current Gain vs. Collector Current

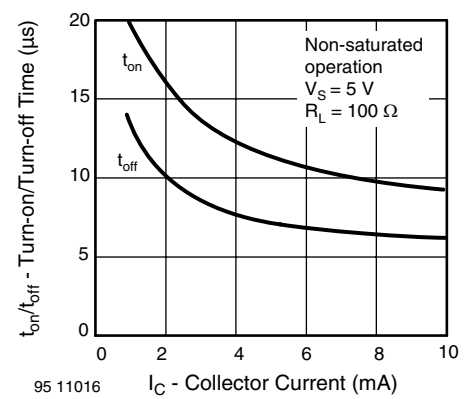
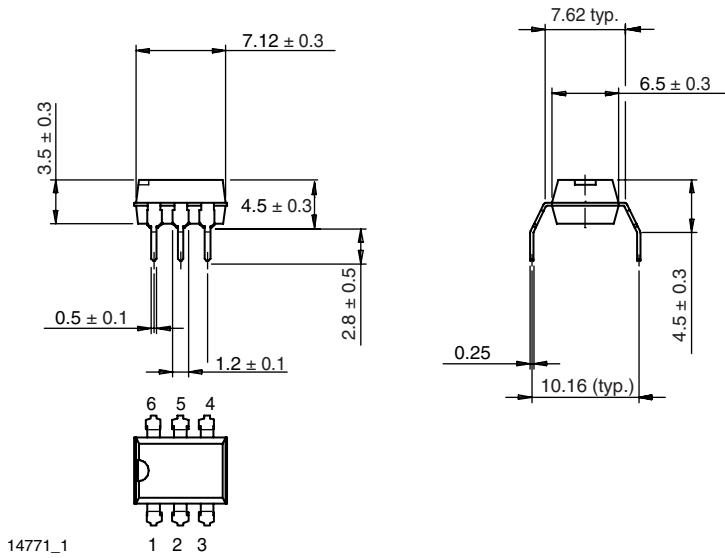


Fig. 17 - Turn-on/off Time vs. Collector Current

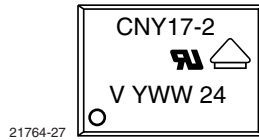


Optocoupler, Phototransistor Output, Vishay Semiconductors  
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**PACKAGE DIMENSIONS** in millimeters



**PACKAGE MARKING**





## Disclaimer

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